High frequency rectifier schottky barrier diode

RB081L−20 *New*

●Applications

High frequency rectification

For switching power supply

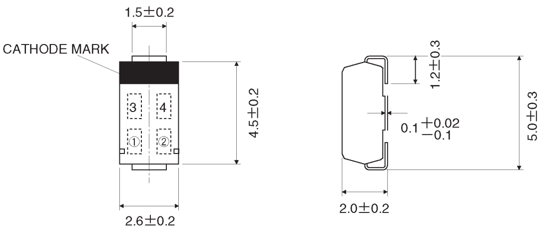
●Features

1) Compact power mold type (PMDS)
2) Extreme low forward voltage
   (typical capability of 0.27V at 1A)
3) I_O = 5A achieved despite the size

●Construction

Silicon epitaxial planar

●External dimensions (Units: mm)



ROHM：PMDS
JEDEC：SOD-106

①, ②······Date of manufacture EX. 1998.4 → 8, 4

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	25	V
DC reverse voltage	V_R	20	V
Mean rectifying current	I_O1 *1	5	A
	I_O2 *2	4	A
Peak forward surge current （60Hz・1∽）	I_{FSM}	70	A
Junction temperature	Tj	125	℃
Storage temperature	Tstg	−40～+125	℃

*1 When mounted on an alumina substrates, Tc Max.＝100℃

*2 When mounted on an alumina substrates, Ta＝25℃

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	0.35	0.45	V	I_F＝5.0A
Reverse current	I_R	0.30	0.7	mA	V_R＝20V

●Electrical characteristic curves (Ta = 25°C unless specified otherwise)

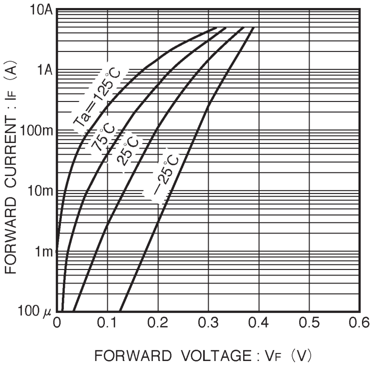


Fig. 1 Forward characteristics

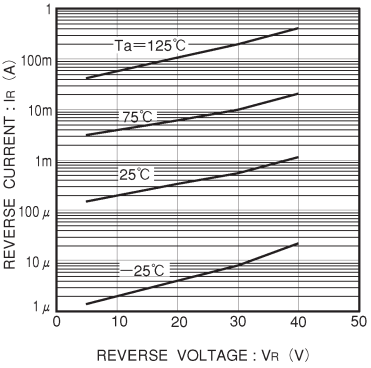


Fig. 2 Reverse characteristics

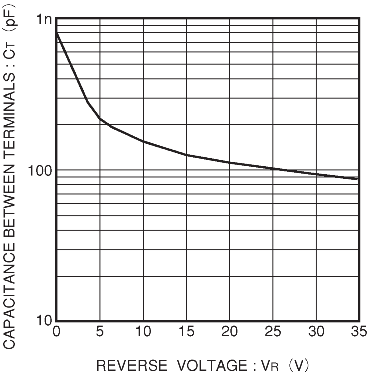


Fig. 3 Capacitance between terminals characteristics